

b1 14. (Amended) The method of claim 24 wherein the gas includes at least one member selected from the group consisting of ammonia, hydrogen and sulfur dioxide.

Please enter new claim 24 as shown below.

--24. (New) A method of enabling the removal of fluorine containing residue from a semiconductor substrate with gas and/or vapor to which the residue is reactive and which need not be in supercritical or dense phase form, comprising the steps of:

b3 applying said gas and/or vapor to which the residue is reactive to the semiconductor substrate while the temperature of the substrate is at an elevated level with respect to ambient temperature; 23°C.
exposing the substrate to ultraviolet radiation provided by an ultraviolet lamp simultaneously with said gas and/or vapor applying step, wherein the applying and exposing steps are continued for a period of time sufficient to render the residue to be soluble in deionized water; and

rinsing the substrate with deionized water.--